

Zainuriah Hassan

List of Publications by Year in descending order

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595
papers

7,664
citations

81743

39
h-index

123241

61
g-index

599
all docs

599
docs citations

599
times ranked

6553
citing authors

#	ARTICLE	IF	CITATIONS
1	InGaN: An overview of the growth kinetics, physical properties and emission mechanisms. Superlattices and Microstructures, 2008, 43, 1-23.	1.4	205
2	Innovative advances in LED technology. Microelectronics Journal, 2005, 36, 129-137.	1.1	184
3	An image encryption scheme based on quantum logistic map. Communications in Nonlinear Science and Numerical Simulation, 2012, 17, 4653-4661.	1.7	161
4	Pseudo random number generator based on quantum chaotic map. Communications in Nonlinear Science and Numerical Simulation, 2014, 19, 101-111.	1.7	154
5	A high-sensitivity room-temperature hydrogen gas sensor based on oblique and vertical ZnO nanorod arrays. Sensors and Actuators B: Chemical, 2013, 176, 360-367.	4.0	142
6	A novel scheme for image encryption based on 2D piecewise chaotic maps. Optics Communications, 2010, 283, 3259-3266.	1.0	127
7	Fabrication and characterization of V ₂ O ₅ nanorods based metal-“semiconductor”-metal photodetector. Sensors and Actuators A: Physical, 2016, 250, 250-257.	2.0	98
8	Structural and optical properties of nanocrystalline CdS thin films prepared using microwave-assisted chemical bath deposition. Thin Solid Films, 2012, 520, 3477-3484.	0.8	97
9	High sensitivity and fast response and recovery times in a ZnO nanorod array/p-Si self-powered ultraviolet detector. Applied Physics Letters, 2012, 101, .	1.5	90
10	High-quality vertically aligned ZnO nanorods synthesized by microwave-assisted CBD with ZnO-PVA complex seed layer on Si substrates. Journal of Alloys and Compounds, 2011, 509, 6711-6719.	2.8	84
11	Room temperature hydrogen gas sensor based on ZnO nanorod arrays grown on a SiO ₂ /Si substrate via a microwave-assisted chemical solution method. Journal of Alloys and Compounds, 2013, 546, 107-111.	2.8	84
12	A high-sensitivity, fast-response, rapid-recovery UV photodetector fabricated based on catalyst-free growth of ZnO nanowire networks on glass substrate. Optical Materials, 2016, 60, 30-37.	1.7	82
13	Enhancement of optical transmittance and electrical resistivity of post-annealed ITO thin films RF sputtered on Si. Applied Surface Science, 2018, 443, 544-547.	3.1	80
14	New optical features to enhance solar cell performance based on porous silicon surfaces. Applied Surface Science, 2011, 257, 6112-6117.	3.1	73
15	Highly sensitive fast-response UV photodiode fabricated from rutile TiO ₂ nanorod array on silicon substrate. Sensors and Actuators A: Physical, 2015, 221, 15-21.	2.0	68
16	Synthesis and characterization of single-crystal CdS nanosheet for high-speed photodetection. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1716-1721.	1.3	67
17	Effective conversion efficiency enhancement of solar cell using ZnO/PS antireflection coating layers. Solar Energy, 2012, 86, 541-547.	2.9	67
18	A high-sensitivity, fast-response, rapid-recovery p-n heterojunction photodiode based on rutile TiO ₂ nanorod array on p-Si(111). Applied Surface Science, 2014, 305, 445-452.	3.1	64

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19	The effect of etching time of porous silicon on solar cell performance. Superlattices and Microstructures, 2011, 50, 647-658.	1.4	63
20	Effects of Postdeposition Annealing in Argon Ambient on Metallorganic Decomposed CeO ₂ Gate Spin Coated on Silicon. Journal of the Electrochemical Society, 2010, 157, H6.	1.3	61
21	Fabrication and characterisations of n-CdS/p-PbS heterojunction solar cells using microwave-assisted chemical bath deposition. Solar Energy, 2013, 89, 143-151.	2.9	60
22	High performance room temperature GaN-nanowires hydrogen gas sensor fabricated by chemical vapor deposition (CVD) technique. International Journal of Hydrogen Energy, 2013, 38, 14085-14101.	3.8	57
23	Fabrication of low cost UV photo detector using ZnO nanorods grown onto nylon substrate. Journal of Materials Science: Materials in Electronics, 2015, 26, 1322-1331.	1.1	57
24	Fabrication and characterization of metal-semiconductor-metal ultraviolet photodetector based on rutile TiO ₂ nanorod. Materials Research Bulletin, 2016, 73, 29-37.	2.7	53
25	Morphological, optical, and Raman characteristics of ZnO nanoflakes prepared via a sol-gel method. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 143-147.	0.8	52
26	High Al-content Al _x Ga _{1-x} N epilayers grown on Si substrate by plasma-assisted molecular beam epitaxy. Journal of Alloys and Compounds, 2009, 487, 24-27.	2.8	51
27	Sm ₂ O ₃ gate dielectric on Si substrate. Materials Science in Semiconductor Processing, 2010, 13, 303-314.	1.9	50
28	High performance CuS p-type thin film as a hydrogen gas sensor. Sensors and Actuators A: Physical, 2016, 249, 68-76.	2.0	50
29	Schottky diode based on porous GaN for hydrogen gas sensing application. Applied Surface Science, 2007, 253, 9525-9528.	3.1	49
30	Broadband anti-reflective properties of grown ZnO nanopyramidal structure on Si substrate via low-temperature electrochemical deposition. Ceramics International, 2016, 42, 5136-5140.	2.3	49
31	Porous GaN prepared by UV assisted electrochemical etching. Thin Solid Films, 2007, 515, 3469-3474.	0.8	48
32	Effects of oxygen percentage on the growth of copper oxide thin films by reactive radio frequency sputtering. Materials Chemistry and Physics, 2013, 140, 243-248.	2.0	47
33	Hydrogen gas sensing performance of GaN nanowires-based sensor at low operating temperature. Sensors and Actuators B: Chemical, 2014, 204, 497-506.	4.0	46
34	Porous GaN on Si(1 1 1) and its application to hydrogen gas sensor. Sensors and Actuators B: Chemical, 2011, 155, 699-708.	4.0	45
35	Characterization of nanocrystalline PbS thin films prepared using microwave-assisted chemical bath deposition. Materials Science in Semiconductor Processing, 2012, 15, 564-571.	1.9	45
36	Structural and photoluminescence studies of rutile TiO ₂ nanorods prepared by chemical bath deposition method on Si substrates at different pH values. Measurement: Journal of the International Measurement Confederation, 2014, 56, 155-162.	2.5	45

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37	Growth of CdS nanosheets and nanowires through the solvothermal method. Journal of Crystal Growth, 2012, 359, 43-48.	0.7	44
38	Fabrication and characterization of ZnO nanorods/p-6H ⁺ SiC heterojunction LED by microwave-assisted chemical bath deposition. Superlattices and Microstructures, 2013, 53, 31-38.	1.4	44
39	Fabrication and characterization of nanocrystalline CdS thin film-based optical sensor grown via microwave-assisted chemical bath deposition. Superlattices and Microstructures, 2014, 67, 8-16.	1.4	43
40	Study of efficient semipolar (11-22) InGaN green micro-light-emitting diodes on high-quality (11-22) GaN/sapphire template. Optics Express, 2019, 27, 24154.	1.7	43
41	Growth of zinc oxide nanoflowers by thermal evaporation method. Physica B: Condensed Matter, 2010, 405, 2570-2572.	1.3	41
42	Ultrathin Wafer Pre-Assembly and Assembly Process Technologies: A Review. Critical Reviews in Solid State and Materials Sciences, 2015, 40, 251-290.	6.8	41
43	Growth and characterization of CdS single-crystalline micro-rod photodetector. Superlattices and Microstructures, 2013, 54, 137-145.	1.4	40
44	Preparation of chemically deposited thin films of CdS/PbS solar cell. Superlattices and Microstructures, 2012, 52, 816-823.	1.4	39
45	ZnO nanocoral reef grown on porous silicon substrates without catalyst. Journal of Alloys and Compounds, 2011, 509, 5627-5630.	2.8	38
46	Growth and characterization of Zn _x Cd _{1-x} S nanoflowers by microwave-assisted chemical bath deposition. Journal of Alloys and Compounds, 2012, 541, 227-233.	2.8	38
47	Microwave-assisted chemical bath deposition of nanocrystalline CdS thin films with superior photodetection characteristics. Sensors and Actuators A: Physical, 2015, 230, 9-16.	2.0	38
48	Fabrication of a highly flexible low-cost H ₂ gas sensor using ZnO nanorods grown on an ultra-thin nylon substrate. Journal of Materials Science: Materials in Electronics, 2016, 27, 9461-9469.	1.1	38
49	Experimental and theoretical studies of surface phonon polariton of AlN thin film. Applied Physics Letters, 2007, 90, 081902.	1.5	37
50	The study of Pt Schottky contact on porous GaN for hydrogen sensing. Thin Solid Films, 2007, 515, 7337-7341.	0.8	37
51	Structural and optical characteristics of porous GaN generated by electroless chemical etching. Materials Letters, 2009, 63, 724-727.	1.3	37
52	The effect of anti-reflection coating of porous silicon on solar cells efficiency. Optik, 2011, 122, 1462-1465.	1.4	37
53	Comparison of metal-organic decomposed (MOD) cerium oxide (CeO ₂) gate deposited on GaN and SiC substrates. Journal of Crystal Growth, 2011, 326, 2-8.	0.7	37
54	Comparative study of ultraviolet detectors based on ZnO nanostructures grown on different substrates. Journal of Applied Physics, 2012, 112, 074510.	1.1	37

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55	Effects of ZnO seed layer thickness on catalyst-free growth of ZnO nanostructures for enhanced UV photoresponse. <i>Optics and Laser Technology</i> , 2018, 98, 344-353.	2.2	37
56	Characterization of surface roughness of Pt Schottky contacts on quaternary n-Al _{0.08} In _{0.08} Ga _{0.84} N thin film assessed by atomic force microscopy and fractal analysis. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 466-477.	1.1	36
57	Effect of zinc acetate dihydrate concentration on morphology of ZnO seed layer and ZnO nanorods grown by hydrothermal method. <i>Colloids and Interface Science Communications</i> , 2020, 38, 100312.	2.0	34
58	Structural, optical and electrical characterization of ITO, ITO/Ag and ITO/Ni transparent conductive electrodes. <i>Applied Surface Science</i> , 2014, 288, 599-603.	3.1	33
59	Hash function based on hierarchy of 2D piecewise nonlinear chaotic maps. <i>Chaos, Solitons and Fractals</i> , 2009, 42, 2405-2412.	2.5	31
60	The structural and optical characterizations of ZnO synthesized using the "bottom-up" growth method. <i>Physica B: Condensed Matter</i> , 2010, 405, 2045-2048.	1.3	31
61	Quaternary ultraviolet AlInGa _N MQW laser diode performance using quaternary AlInGa _N electron blocking layer. <i>Optics Express</i> , 2011, 19, 9245.	1.7	31
62	Porous Si(111) and Si(100) as an intermediate buffer layer for nanocrystalline InN films. <i>Journal of Alloys and Compounds</i> , 2009, 479, L54-L58.	2.8	30
63	PbS nanocrystal solar cells fabricated using microwave-assisted chemical bath deposition. <i>International Journal of Hydrogen Energy</i> , 2013, 38, 807-815.	3.8	30
64	Influence of CuS membrane annealing time on the sensitivity of EGFET pH sensor. <i>Materials Science in Semiconductor Processing</i> , 2017, 71, 217-225.	1.9	30
65	Effect of Postdeposition Annealing in Oxygen Ambient on Gallium-Nitride-Based MOS Capacitors With Cerium Oxide Gate. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 122-131.	1.6	29
66	Influence of deposition temperature on the growth of rutile TiO ₂ nanostructures by CBD method on seed layer prepared by RF magnetron sputtering. <i>Superlattices and Microstructures</i> , 2013, 64, 27-36.	1.4	29
67	Characterization Methods for Ultrathin Wafer and Die Quality: A Review. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2014, 4, 2042-2057.	1.4	29
68	Free growth of one-dimensional $\hat{\Gamma}^2$ -Ga ₂ O ₃ nanostructures including nanowires, nanobelts and nanosheets using a thermal evaporation method. <i>Ceramics International</i> , 2016, 42, 13343-13349.	2.3	29
69	Effect of different EBL structures on deep violet InGa _N laser diodes performance. <i>Optics and Laser Technology</i> , 2016, 76, 106-112.	2.2	29
70	Influences of substrate type on the pH sensitivity of CuS thin films EGFET prepared by spray pyrolysis deposition. <i>Materials Science in Semiconductor Processing</i> , 2017, 63, 269-278.	1.9	28
71	Novel SnO ₂ -coated $\hat{\Gamma}^2$ -Ga ₂ O ₃ nanostructures for room temperature hydrogen gas sensor. <i>International Journal of Hydrogen Energy</i> , 2021, 46, 7000-7010.	3.8	28
72	A review of laser ablation and dicing of Si wafers. <i>Precision Engineering</i> , 2022, 73, 377-408.	1.8	28

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73	Growth and characterization of rutile TiO ₂ nanorods on various substrates with fabricated fast-response metal-semiconductor-metal UV detector based on Si substrate. <i>Superlattices and Microstructures</i> , 2015, 83, 549-564.	1.4	27
74	Effects of ammonia ambient annealing on physical and electrical characteristics of rare earth CeO ₂ as passivation film on silicon. <i>Journal of Alloys and Compounds</i> , 2017, 695, 3104-3115.	2.8	27
75	Surface and interface phonon polaritons of wurtzite GaN thin film grown on 6H-SiC substrate. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	26
76	Improved performance of solar cell based on porous silicon surfaces. <i>Optik</i> , 2011, 122, 2075-2077.	1.4	26
77	Porous silicon nanowires fabricated by electrochemical and laser-induced etching. <i>Journal of Materials Science: Materials in Electronics</i> , 2011, 22, 717-723.	1.1	26
78	Characterizations of InN Thin Films Grown on Si (110) Substrate by Reactive Sputtering. <i>Journal of Nanomaterials</i> , 2011, 2011, 1-7.	1.5	26
79	Microwave assisted chemical bath deposition of vertically aligned ZnO nanorods on a variety of substrates seeded by PVA-Zn(OH) ₂ nanocomposites. <i>Applied Surface Science</i> , 2012, 258, 4467-4472.	3.1	26
80	High-performance n heterojunction photodetectors based on V ₂ O ₅ nanorods by spray pyrolysis. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	1.1	26
81	Investigation of forming-gas annealed CeO ₂ thin film on GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2011, 22, 583-591.	1.1	25
82	Fabrication of Tungsten Oxide Nanostructure by Sol-Gel Method. <i>Procedia Chemistry</i> , 2016, 19, 113-118.	0.7	25
83	Recent advances and challenges in the MOCVD growth of indium gallium nitride: A brief review. <i>Materials Science in Semiconductor Processing</i> , 2022, 143, 106545.	1.9	25
84	MBE growth of GaN pn-junction photodetector on AlN/Si(111) substrate with Ni/Ag as ohmic contact. <i>Superlattices and Microstructures</i> , 2013, 56, 35-44.	1.4	24
85	Fabrication of ZnO nanorod/p-GaN high-brightness UV LED by microwave-assisted chemical bath deposition with Zn(OH) ₂ -PVA nanocomposites as seed layer. <i>Optical Materials</i> , 2013, 35, 1035-1041.	1.7	24
86	Growth and conversion of In ₂ -Ga ₂ O ₃ nanobelts into GaN nanowires via catalyst-free chemical vapor deposition technique. <i>Superlattices and Microstructures</i> , 2013, 54, 215-224.	1.4	24
87	Optical properties of CdS micro/nanocrystalline structures prepared via a thermal evaporation method. <i>Materials Science in Semiconductor Processing</i> , 2014, 26, 87-92.	1.9	24
88	Rapid Formation and Evolution of Anodized-Zn Nanostructures in NaHCO ₃ Solution. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, M105-M112.	0.9	24
89	Synthesis and characterization of nanocrystalline CdS thin films for highly photosensitive self-powered photodetector. <i>EPJ Applied Physics</i> , 2016, 74, 10101.	0.3	24
90	Effect of Annealing Time of YAG:Ce ³⁺ Phosphor on White Light Chromaticity Values. <i>Journal of Electronic Materials</i> , 2018, 47, 1638-1646.	1.0	24

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91	Surface phonon polariton of wurtzite GaN thin film grown on \bar{c} -plane sapphire substrate. Solid State Communications, 2008, 145, 535-538.	0.9	23
92	Structural Properties of Doped GaN on Si(111) Studied by X-Ray Diffraction Techniques. Journal of Nondestructive Evaluation, 2009, 28, 125-130.	1.1	23
93	Enhancing photoresponse time of low cost Pd/ZnO nanorods prepared by thermal evaporation techniques for UV detection. Applied Surface Science, 2011, 258, 461-465.	3.1	23
94	Effects of N ₂ O Postdeposition Annealing on Metal-Organic Decomposed CeO ₂ Gate Oxide Spin-Coated on GaN Substrate. Journal of the Electrochemical Society, 2011, 158, H423.	1.3	23
95	Pt-decorated GaN nanowires with significant improvement in H ₂ gas-sensing performance at room temperature. Journal of Colloid and Interface Science, 2015, 460, 135-145.	5.0	23
96	Growth of GaN on sputtered GaN buffer layer via low cost and simplified sol-gel spin coating method. Vacuum, 2015, 119, 119-122.	1.6	23
97	Effects of thermal treatment on the anodic growth of tungsten oxide films. Thin Solid Films, 2015, 588, 44-49.	0.8	23
98	Catalyst-free growth of ZnO nanowires on ITO seed layer/glass by thermal evaporation method: Effects of ITO seed layer laser annealing temperature. Superlattices and Microstructures, 2016, 92, 68-79.	1.4	23
99	Investigation of structural and optical properties of nanoporous GaN film. Applied Surface Science, 2007, 253, 7429-7434.	3.1	22
100	Fabrication and characterization of nanocrystalline n-CdO/p-Si as a solar cell. Superlattices and Microstructures, 2012, 52, 800-806.	1.4	22
101	Synthesis of wurtzite GaN thin film via spin coating method. Materials Science in Semiconductor Processing, 2014, 17, 63-66.	1.9	22
102	Alteration of structural and optical properties in quaternary Al _{0.1} In _{0.1} Ga _{0.8} N films using ultraviolet assisted photo-electrochemical etching route. Journal of Alloys and Compounds, 2015, 649, 337-347.	2.8	22
103	Effect of Annealing on the Electrical Properties of Cu _x S Thin Films. Procedia Chemistry, 2016, 19, 15-20.	0.7	22
104	Self-powered UV photodetector performance optimization based on Ag nanoparticles-encapsulated-ZnO nanorods by photo-deposition method. Sensors and Actuators A: Physical, 2021, 331, 113032.	2.0	22
105	Effect of hydrostatic pressure on the barrier height of Ni Schottky contacts on n-AlGaIn. Applied Physics Letters, 2006, 88, 022109.	1.5	21
106	Surface phonon polariton mode of wurtzite structure Al _x Ga _{1-x} N thin films. Applied Physics Letters, 2007, 91, .	1.5	21
107	Effect of Al mole fraction on structural and electrical properties of Al _x Ga _{1-x} N/GaN heterostructures grown by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2011, 257, 4159-4164.	3.1	21
108	Effects of annealing on the optical and electrical properties of CdO thin films prepared by thermal evaporation. Materials Letters, 2013, 105, 84-86.	1.3	21

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109	Al _x Ga _{1-x} N/GaN/AlN heterostructures grown on Si(111) substrates by MBE for MSM UV photodetector applications. <i>Materials Science in Semiconductor Processing</i> , 2015, 34, 214-223.	1.9	21
110	High sensitivity extended gate effect transistor based on V ₂ O ₅ nanorods. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 1364-1369.	1.1	21
111	A novel porous silicon multi-ions selective electrode based extended gate field effect transistor for sodium, potassium, calcium, and magnesium sensor. <i>Applied Physics A: Materials Science and Processing</i> , 2019, 125, 1.	1.1	21
112	Ultraviolet electroluminescence from flowers-like n-ZnO nanorods/p-GaN light-emitting diode fabricated by modified chemical bath deposition. <i>Journal of Luminescence</i> , 2020, 226, 117510.	1.5	21
113	MOS Characteristics of Metallorganic-Decomposed CeO ₂ Spin-Coated on GaN. <i>Electrochemical and Solid-State Letters</i> , 2010, 13, H116.	2.2	20
114	Stiffness properties of porous silicon nanowires fabricated by electrochemical and laser-induced etching. <i>Superlattices and Microstructures</i> , 2011, 50, 119-127.	1.4	20
115	Nanocrystalline ZnO film grown on porous silicon layer by radio frequency sputtering system. <i>Materials Letters</i> , 2012, 68, 51-53.	1.3	20
116	Structural and optical properties of nanocrystalline lead sulfide thin films prepared by microwave-assisted chemical bath deposition. <i>Materials Science in Semiconductor Processing</i> , 2013, 16, 971-979.	1.9	20
117	Effects of variations in precursor concentration on the growth of rutile TiO ₂ nanorods on Si substrate with fabricated fast-response metal-semiconductor-metal UV detector. <i>Optical Materials</i> , 2015, 44, 37-47.	1.7	20
118	Characterization of V ₂ O ₅ nanorods grown by spray pyrolysis technique. <i>Journal of Materials Science: Materials in Electronics</i> , 2016, 27, 4613-4621.	1.1	20
119	Effect of temperature on hydrothermally grown high-quality single-crystals Mg-doped ZnO nanorods for light-emitting diode application. <i>Journal of Luminescence</i> , 2017, 192, 634-643.	1.5	20
120	Cost-effective single-step carbon nanotube synthesis using microwave oven. <i>Materials Research Express</i> , 2017, 4, 085602.	0.8	20
121	Fabrication of ultra-violet photodetector with enhanced optoelectronic parameters using low-cost F-doped ZnO nanostructures. <i>Sensors and Actuators A: Physical</i> , 2021, 332, 113092.	2.0	20
122	The effect of porosity on the properties of silicon solar cell. <i>Microelectronics International</i> , 2010, 27, 117-120.	0.4	19
123	Analytical and visual modeling of InGaN/GaN single quantum well laser based on rate equations. <i>Optics and Laser Technology</i> , 2012, 44, 12-20.	2.2	19
124	Porous WO ₃ formed by anodization in oxalic acid. <i>Journal of Porous Materials</i> , 2013, 20, 997-1002.	1.3	19
125	Improvement of the performance characteristics of deep violet InGaN multi-quantum-well laser diodes using step-graded electron blocking layers and a delta barrier. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	19
126	Fabrication of Cu ₂ O nanocrystalline thin films photosensor prepared by RF sputtering technique. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2017, 94, 132-138.	1.3	19

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127	The growth of III-V nitrides heterostructure on Si substrate by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2010, 506, 343-346.	2.8	18
128	High-quality GaN nanowires grown on Si and porous silicon by thermal evaporation. <i>Applied Surface Science</i> , 2012, 263, 50-53.	3.1	18
129	Low-power UV photodetection characteristics of ZnO tetrapods grown on catalyst-free glass substrate. <i>Sensors and Actuators A: Physical</i> , 2016, 250, 187-194.	2.0	18
130	Sensitivity of CuS and CuS/ITO EGFETs implemented as pH sensors. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	1.1	18
131	Large-scale uniform ZnO tetrapods on catalyst free glass substrate by thermal evaporation method. <i>Materials Research Bulletin</i> , 2016, 79, 63-68.	2.7	18
132	Photoelectrochemical ultraviolet photodetector by anodic titanium dioxide nanotube layers. <i>Sensors and Actuators A: Physical</i> , 2018, 279, 263-271.	2.0	18
133	GaN Schottky barrier photodiode on Si (111) with low-temperature-grown cap layer. <i>Journal of Alloys and Compounds</i> , 2009, 481, L15-L19.	2.8	17
134	Nano and micro porous GaN characterization using image processing method. <i>Optik</i> , 2012, 123, 1074-1078.	1.4	17
135	Growth and characterization of different structured CdO using a vapor transport. <i>Materials Letters</i> , 2013, 102-103, 12-14.	1.3	17
136	Synthesis of two-dimensional gallium nitride via spin coating method: influences of nitridation temperatures. <i>Journal of Sol-Gel Science and Technology</i> , 2013, 68, 95-101.	1.1	17
137	Surface phonon polariton characteristic of honeycomb nanoporous GaN thin films. <i>Applied Physics Letters</i> , 2013, 102, 101601.	1.5	17
138	Investigation of structural and optical properties of GaN on flat and porous silicon. <i>Superlattices and Microstructures</i> , 2016, 97, 586-590.	1.4	17
139	Effects of post-deposition annealing temperature in nitrogen/oxygen/nitrogen ambient on polycrystalline gallium oxide films. <i>Applied Surface Science</i> , 2021, 550, 149340.	3.1	17
140	Performance and optical characteristic of InGaN MQWs laser diodes. <i>Optics Express</i> , 2007, 15, 2380.	1.7	16
141	Room-temperature hydrogen gas sensor with ZnO nanorod arrays grown on a quartz substrate. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012, 46, 254-258.	1.3	16
142	AlN/GaN/AlN heterostructures grown on Si substrate by plasma-assisted MBE for MSM UV photodetector applications. <i>Materials Science in Semiconductor Processing</i> , 2015, 29, 231-237.	1.9	16
143	Passivation of silicon substrate using two-step grown ternary aluminium doped zirconium oxide. <i>Applied Surface Science</i> , 2019, 493, 411-422.	3.1	16
144	Characteristics of low-temperature-grown GaN films on Si(111). <i>Solid State Communications</i> , 2005, 133, 283-287.	0.9	15

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145	High carrier concentrations of n- and p-doped GaN on Si(111) by nitrogen plasma-assisted molecular-beam epitaxy. <i>Journal of Materials Research</i> , 2007, 22, 2623-2630.	1.2	15
146	Improved performance of a crystalline silicon solar cell based on ZnO/PS anti-reflection coating layers. <i>Superlattices and Microstructures</i> , 2011, 50, 517-528.	1.4	15
147	Fast UV detection and hydrogen sensing by ZnO nanorod arrays grown on a flexible Kapton tape. <i>Materials Science-Poland</i> , 2013, 31, 180-185.	0.4	15
148	Sensing devices based on ZnO hexagonal tube-like nanostructures grown on p-GaN heterojunction by wet thermal evaporation. <i>Thin Solid Films</i> , 2013, 540, 212-220.	0.8	15
149	Plasma-assisted MBE growth of AlN/GaN/AlN heterostructures on Si (111) substrate. <i>Superlattices and Microstructures</i> , 2013, 60, 500-507.	1.4	15
150	Fabrication of InN based photodetector using porous silicon buffer layer. <i>Surface Engineering</i> , 2013, 29, 772-777.	1.1	15
151	Characteristics of MSM photodetector fabricated on porous In _{0.08} Ga _{0.92} N. <i>Measurement: Journal of the International Measurement Confederation</i> , 2014, 50, 172-174.	2.5	15
152	A novel CuS thin film deposition method by laser-assisted spray photolysis deposition and its application to EGFET. <i>Sensors and Actuators B: Chemical</i> , 2017, 247, 197-215.	4.0	15
153	Growth and characterization of GaN nanostructures under various ammoniating time with fabricated Schottky gas sensor based on Si substrate. <i>Superlattices and Microstructures</i> , 2018, 117, 92-104.	1.4	15
154	Dark current characteristics of thermally treated contacts on GaN-based ultraviolet photodetectors. <i>Microelectronic Engineering</i> , 2005, 81, 262-267.	1.1	14
155	Effect of post-deposition annealing temperature on CeO ₂ thin film deposited on silicon substrate via RF magnetron sputtering technique. <i>Materials Science in Semiconductor Processing</i> , 2011, 14, 101-107.	1.9	14
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